

**REMARKS**

In the present Amendment, claim 1 was amended to recite that the semiconductor layer is not present in a thickness of greater than 5  $\mu\text{m}$  at a distance of at least 0.2 mm from the anode lead-connection point on the sintered body surface. Support is found, for example, in Fig. 1 and page 3, lines 8-17 of the specification. Claim 4 was amended to recite that wherein the electrically conducting oxide is niobium oxide. New claim 16 was added. Support for claim 16 is found, for example, in Figure 1 and at page 13, lines 22-30 of the specification. No new matter has been added, and entry of the Amendment is respectfully requested.

Upon entry of the Amendment, claims 1-2, 4 and 7-16 will be pending.

The Examiner objected to claim 4, noting that claim 1 excludes aluminum, titanium, or niobium oxide.

As claimed in claim 1, a dielectric oxide film layer, a semiconductor layer and an electrically conducting layer are sequentially stacked on a surface of a valve-acting metal sintered body or electrically conductive oxide sintered body. Claim 1 further defines the valve-acting metal sintered body as being a tantalum sintered body. However, claim 1 still encompasses “electrically conducting oxide sintered body.” Accordingly, claim 4 was amended to recite “wherein the electrically conducting oxide is niobium oxide.” Withdrawal of the objection to claim 4 is respectfully requested.

Claims 1, 2, 4, 7 and 12-15 were rejected under 35 U.S.C. § 103(a) as being unpatentable over Nakamura (US 6,333,844) in view of Shiga et al (WO 02/11932).

Applicants submit that this rejection should be withdrawn because Nakamura and Shiga et al do not disclose or render obvious the present invention, either alone or in combination.

Nakamura discloses in Fig. 1a, a solid electrolyte capacitor comprising a jacketed capacitor element, the capacitor element being obtained by sequentially stacking a dielectric oxide film layer (14), a manganese dioxide layer (15) and an electrically conducting layer (16-18) on a surface of a valve-acting metal sintered body (such as Ta) connected with an anode lead (see Fig. 1). Further, the thickness of the semiconductor layer in the portion excluding the vicinity of the anode lead-connection point is from 20-30  $\mu\text{m}$  (see col. 4, lines 45-54).

However, Nakamura does not teach or suggest that “the semiconductor layer is not present in a thickness of greater than 5  $\mu\text{m}$  at a distance of at least 0.2 mm from the anode lead-connection point on the sintered body surface” as recited in present claim 1 as amended.

Shiga et al is cited as teaching the use of a tantalum powder sintered body having a CV of 100,000  $\mu\text{F V/g}$  or more (see abstract). Shiga et al does not make up for the deficiencies of Nakamura.

Applicant has found that, by specifying the thickness of the semiconductor layer, the generation rate of solid electrolyte capacitors having an extremely large LC value can be decreased. See, page 3, lines 3-17 and page 28, lines 7-13 of the specification.

Nakamura and Shiga et al do not teach or suggest this feature of the present invention.

In view of the above, reconsideration and withdrawal of the §103(a) rejection of claims 1, 2, 4, 7 and 12-15 based on Nakamura in view of Shiga et al are respectfully requested.

Claims 1, 2, 4 and 7-13 were rejected under 35 U.S.C. § 103(a) as being unpatentable over JP 11-067602 (“JP ‘602”) in view of Shiga et al.

Applicants submit that this rejection should be withdrawn because JP ‘602 and Shiga et al do not disclose or render obvious the present invention, either alone or in combination.

Figure 1 in JP ‘602 illustrates a solid electrolyte capacitor which includes an anode 12, a dielectric layer 13 formed thereon and a conductive polymer layer 15 adjacent to the dielectric layer 13. The anode 12 can be a tantalum sintered compact [0050]. A dielectric layer may be the oxide film of a valve metal [0022] and 3,4-ethylenedioxothiophene is mentioned as the conductive polymer [0020]. The conductive polymer layer has a thickness of 10 µm or more (claim 2).

However, JP ‘602 does not teach or suggest that “the semiconductor layer is not present in a thickness of greater than 5 µm at a distance of at least 0.2 mm from the anode lead-connection point on the sintered body surface” as recited in present claim 1 as amended.

Shiga et al is cited as teaching the use of a tantalum powder sintered body having a CV of 100,000 µF V/g or more (see abstract). Shiga et al does not make up for the deficiencies of JP ‘602.

As discussed above, Applicant has found that, by specifying the thickness of the semiconductor layer, the generation rate of solid electrolyte capacitors having an extremely large LC value can be decreased. See, page 3, lines 3-17 and page 28, lines 7-13 of the specification.

JP ‘602 and Shiga et al do not teach or suggest this feature of the present invention.

In view of the above, reconsideration and withdrawal of the §103(a) rejection of claims 1, 2, 4 and 7-13 based on JP ‘602 in view of Shiga et al are respectfully requested.

Allowance is respectfully requested. If any points remain in issue which the Examiner feels may be best resolved through a personal or telephone interview, the Examiner is kindly requested to contact the undersigned at the telephone number listed below.

The USPTO is directed and authorized to charge all required fees, except for the Issue Fee and the Publication Fee, to Deposit Account No. 19-4880. Please also credit any overpayments to said Deposit Account.

Respectfully submitted,

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